CLAIMS:

1. An apparatus comprising:

a substrate; and

an integrated circuit (IC) structure disposed on the substrate, the IC structure including a magnetic layer, wherein:

the magnetic layer has a first portion that is implanted with a dopant and a second portion that is not implanted with the dopant; and

the first portion has a magnetic moment that is less than a magnetic moment of the second portion, wherein the magnetic moment of the first portion is non-zero;

a tunnel barrier layer below the magnetic layer; and

a barrier layer on the magnetic layer, wherein a portion of the barrier layer on the magnetic layer includes the dopant, and the tunnel barrier layer below the magnetic layer is free of the dopant.

2. The apparatus of claim 1, wherein:

the magnetic layer includes a metal selected from a group consisting of cobalt (Co), iron (Fe), nickel (Ni), and an alloy of two or more of Co, Fe, or Ni with or without boron (B).

3. The apparatus of claim 1, wherein the substrate is a semiconductor substrate and the IC structure further comprises:

one or more magnetic base layers disposed on the semiconductor substrate and below the tunnel barrier layer.

4. The apparatus of claim 1, further comprising:

a dielectric material in direct contact with the first portion of the magnetic layer.

5. The apparatus of claim 1, further comprising:

an electrode disposed on the magnetic layer.

6. A computing device comprising:

a circuit board; and

a die coupled with the circuit board, the die including:

a substrate; and

an integrated circuit (IC) structure disposed on the substrate, the IC structure including a magnetic layer, wherein:

the magnetic layer has a first portion that is implanted with a dopant and a second portion that is not implanted with the dopant; and

the first portion has a magnetic moment that is less than a magnetic moment of the second portion, wherein the magnetic moment of the first portion is non-zero;

a tunnel barrier layer below the magnetic layer; and

a barrier layer on the magnetic layer, wherein a portion of the barrier layer on the magnetic layer includes the dopant, and the tunnel barrier layer below the magnetic layer is free of the dopant.

7. The computing device of claim 6, wherein:

the die comprises magnetic random access memory (MRAM); and

the computing device is a mobile computing device including one or more of an antenna, a display, a touchscreen display, a touchscreen controller, a battery, an audio codec, a video codec, a power amplifier, a global positioning system (GPS) device, a compass, a Geiger counter, an accelerometer, a gyroscope, a speaker, and a camera.

8. The computing device of claim 6, wherein the magnetic layer includes a metal selected from a group consisting of cobalt (Co), iron (Fe), nickel (Ni), and an alloy of two or more of Co, Fe, or Ni with or without boron (B).

9. The computing device of claim 6, wherein the die further comprises: one or more magnetic base layers disposed on the substrate and below the tunnel barrier layer.